

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) F03-354-USDiv	Application Number 10/634,836		
				Applicant(s) Hisaki KATO, et al.		Filing Date August 6, 2003	Group Art Unit -2822- 1656
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER <i>UIPE</i> <i>JUL 06 2005</i> <i>PATENTS & TRADEMARK OFFICE</i>	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
U.S. PATENT APPLICATION PUBLICATIONS							
EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES
CMK		H7-7182	01/10/99	Japan			Abs
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
CMK		Japanese Office Action, dated May 24, 2005, with partial English translation					
CMK		NAKAMURA, et al., "Ridge-geometry InGaN multi-quantum-well-structure laser diodes", APPLIED PHYSICS LETTERS, September 2, 1996, Vol. 69, No. 10, pp. 1477-1479					
EXAMINER	<i>CMK/jm</i>			DATE CONSIDERED	11/10/05		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							